

## ABSTRACT OF THE DISCLOSURE

A substrate treating method and apparatus are disclosed, which are capable of treating substrates having a material of high dielectric constant, reliably at a relatively  
5 low temperature. A treating solution containing sulfuric acid ( $\text{H}_2\text{SO}_4$ ) and hydrofluoric acid (HF) or sulfuric acid ( $\text{H}_2\text{SO}_4$ ) and buffered hydrofluoric acid ( $\text{NH}_4\text{F} \cdot \text{HF}$ ) is used for treating substrates coated with a film including the material of high dielectric constant. The material of high  
10 dielectric constant may be treated selectively by the treating solution at the relatively low temperature.